

In re Application of Takanhiro Ohnakado
Application No. Unassigned

IN THE ABSTRACT

Replace the abstract with:

Abstract of the Disclosure

A sophisticated and highly reliable high-frequency Si-MOS semiconductor device having high electrostatic discharge (ESD) resistance. Lateral polysilicon diodes are connected between high-frequency I/O signal lines and the external supply voltage, VDD, and between the ground, GND, and the high-frequency I/O signal lines, respectively. The forward direction of the diodes is the direction from the high-frequency I/O signal line to the supply voltage, VDD, and the direction from the ground, GND, to the high-frequency I/O signal line, respectively.

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